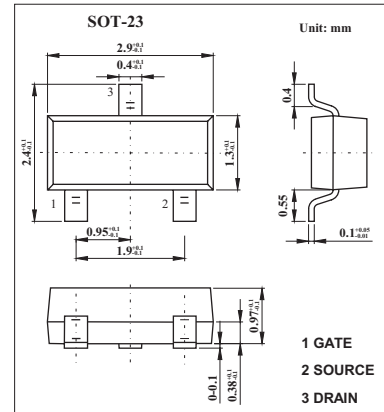


■ Features

- Directly driven by Ics having a 5V power supply.
- Not necessary to consider driving current because of its high input impedance.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage	V _{DSS}	100	V
Gate to source voltage	V _{GSS}	±20	V
Drain current (DC)	I _D	±100	mA
Drain current(pulse) *	I _D	±200	mA
Power dissipation	P _D	2.0	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* PW ≤ 10ms, duty cycle ≤ 5%

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit	
Drain cut-off current	I _{DSS}	V _{DS} =100V, V _{GS} =0			10	μA	
Gate leakage current	I _{GSS}	V _{GS} =±20V, V _{DS} =0			±1.0	μA	
Gate to source cutoff voltage	V _{GS(off)}	V _{DS} =5V, I _D =1 μA	0.8	1.5	1.8	V	
Forward transfer admittance	Y _{fs}	V _{DS} =5.0V, I _D =10mA	20	38		ms	
Drain to source on-state resistance	R _{DS(on)}	V _{GS} =4.0V, I _D =10mA		19	30	Ω	
		V _{GS} =10V, I _D =10mA		15	25	Ω	
Input capacitance	C _{iss}	V _{DS} =5.0V, V _{GS} =0, f=1MHZ		16		pF	
Output capacitance	C _{oss}			12		pF	
Reverse transfer capacitance	C _{rss}			3		pF	
Turn-on delay time	t _{d(on)}				17		ns
Rise time	t _r	I _D =10mA, V _{GS(on)} =5.0V, R _L =500 Ω, V _{DD} =5V, R _G =10 Ω		10		ns	
Turn-off delay time	t _{d(off)}				68		ns
Fall time	t _f				38		ns

■ Marking

Marking	G17
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